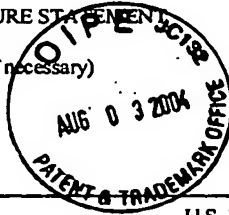


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119330APPLICATION NO.
10/814,169

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

APPLICANT
Satoshi INOUEFILING DATE
April 1, 2004GROUP
2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

	1	"Single Crystal Thin Film Transistors", IBM Technical Disclosure Bulletin, Aug. 1993, p. 257.
	2	R. Ishihara et al., "Advanced Excimer-Laser Crystallization Techniques of Si Thin-Film For Location Control of Large Grain on Glass", proc. SPIE 2001, Vol. 4295, pp. 14-23.

EXAMINER

DATE CONSIDERED

11/5/05

Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Date: August 3, 2004